

Description

Glass passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

Symbol 		Simplified outline  TO-220	
Pin	Description		
1	Cathode		
2	Anode		
3	Gate		

Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

Features

- ◆ Blocking voltage to 800 V
- ◆ On-state RMS current to 4 A
- ◆ Ultra low gate trigger current

SYMBOL	PARAMETER		Value	Unit
V_{DRM}	Repetitive peak off-state voltages	500R	500	V
V_{RRM}		600R	600	
		800R	800	
$I_T (RMS)$	RMS on-state current		4	A
I_{TSM}	Non-repetitive peak on-state current		35	A

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{th j-mb}$	Thermal resistance Junction to mounting base		-	-	2.5	K/W
$R_{th j-a}$	Thermal resistance Junction to ambient	In free air	-	60	-	K/W

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Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{DRM} V_{RRM}	Repetitive peak off-state Voltages	500R 600R 800R	-	500 600 800	V
I_{TAV}	Average on-state current	Half sine wave; $T_{mb} \leq 113^{\circ}C$	-	2.5	A
$I_{T(RMS)}$	RMS on-state current	All conduction angles	-	4	A
I_{TSM}	Non-repetitive peak On-state current	half sine wave; $T_j = 25^{\circ}C$ prior to surge	-	35	A
		T=10ms T=8.3ms	-	38	A
I^2t	I^2t for fusing	T=10ms	-	6.1	A ² S
DI_T/dt	Repetitive rate of rise of on-state current after trigering	$I_{TM}=10A$; $I_G=50mA$; $D_{IG}/dt=50mA/\mu s$	-	50	A/ μs
I_{GM}	Peak gate current		-	2	A
V_{GM}	Peak gate voltage		-	5	V
P_{GM}	Peak gate power		-	5	W
$P_{G(AV)}$	Average gate power	Over any 20 ms period	-	0.5	W
T_{stg}	Storage temperature		-40	150	$^{\circ}C$
T_j	Operating junction Temperature		-	125 ²	$^{\circ}C$

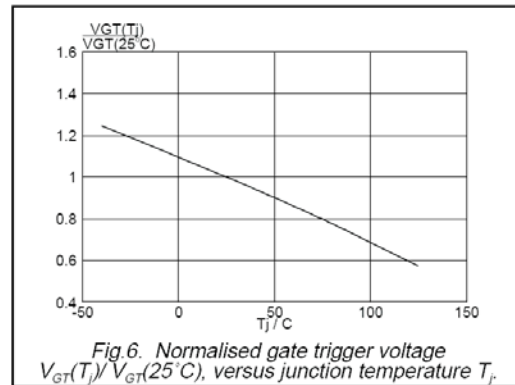
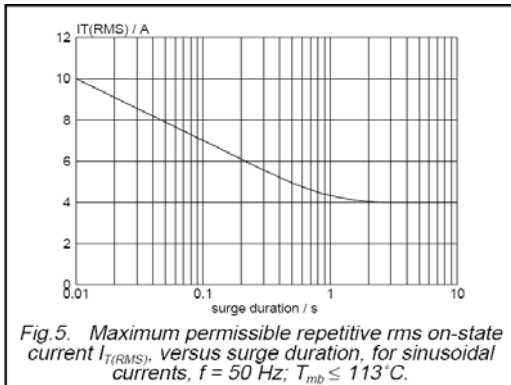
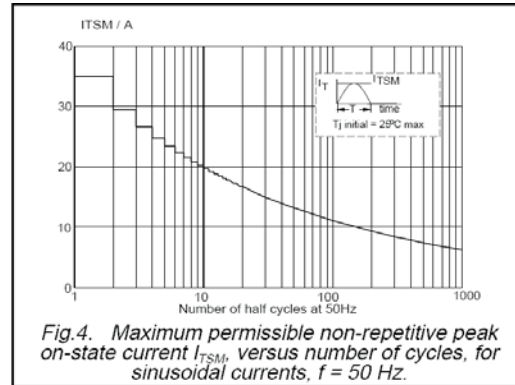
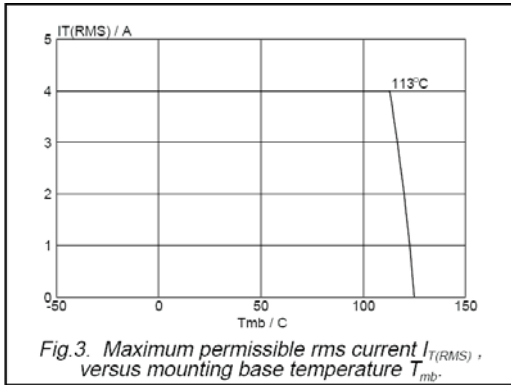
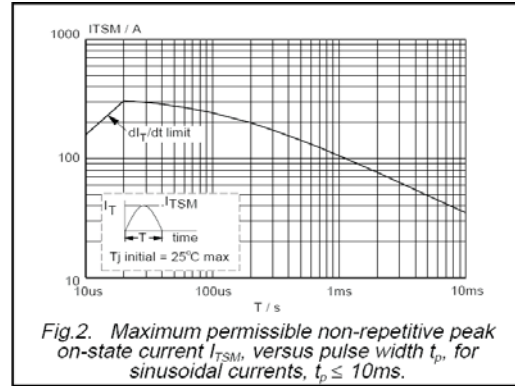
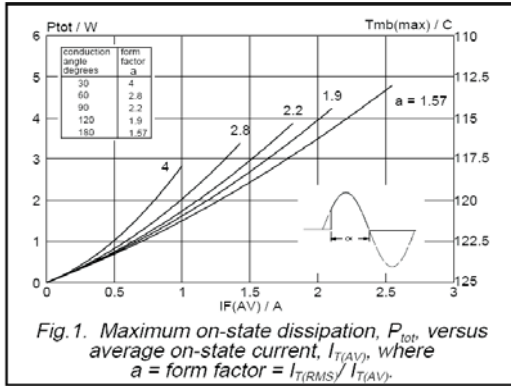
$T_j=25^{\circ}C$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT}	Gate trigger current	$V_D=12V$; $I_T=0.1A$	-	15	200	μA
I_L	Latching current	$V_D=12V$; $I_{GT}=0.1A$	-	0.17	10	mA
I_H	Holding current	$V_D=12V$; $I_{GT}=0.1A$	-	0.10	6	mA
V_T	On-state voltage	$I_T=5A$	-	1.23	1.8	V
V_{GT}	Gate trigger voltage	$V_D=12V$; $I_T=0.1A$ $V_D=V_{DRM(max)}$; $I_T=0.1A$; $T_j=110^{\circ}C$	- 0.1	0.4 0.2	1.5 -	V V
I_D	Off-state leakage current	$V_D=V_{DRM(max)}$; $V_R=V_{RRM(max)}$; $T_j=125^{\circ}C$	-	0.1	0.5	mA

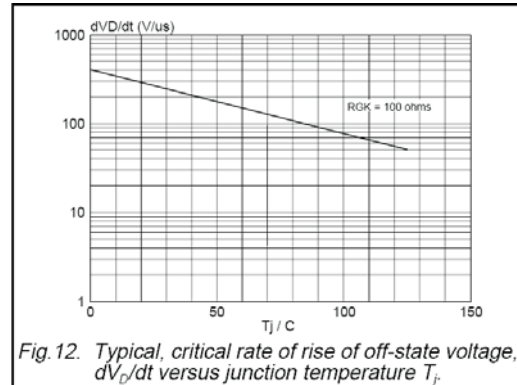
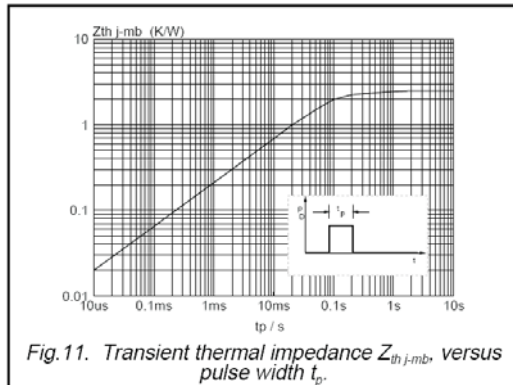
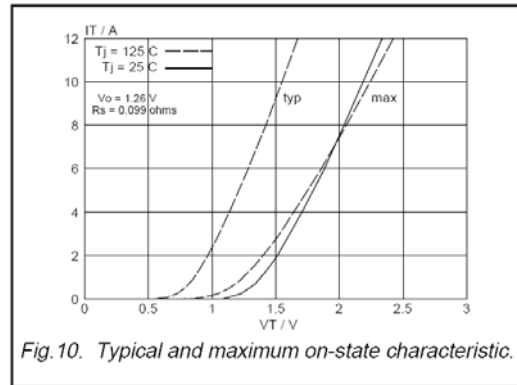
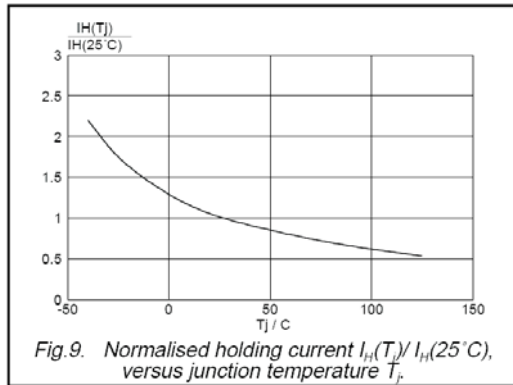
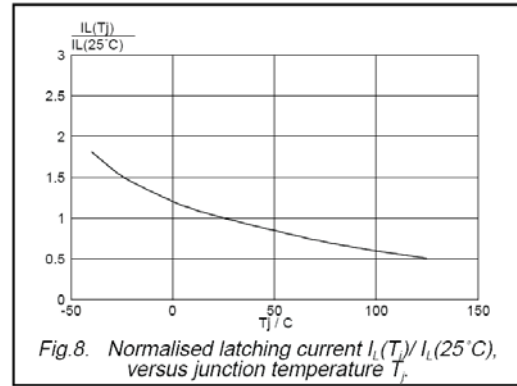
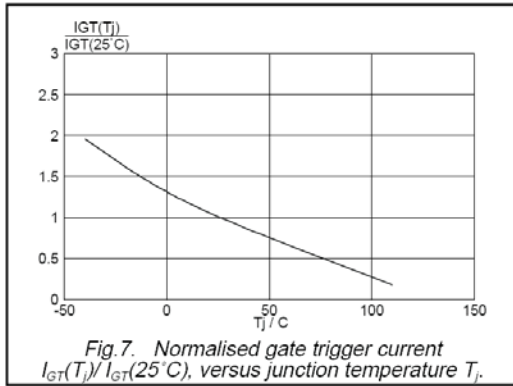
Dynamic Characteristics

D_{VD}/dt	Critical rate of rise of Off-state voltage	$V_{DM}=67\% V_{DRM(max)}$; $T_j=125^{\circ}C$; Exponential wave form; $R_{GK}=100\Omega$	-	50	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM}=10A$; $V_D=V_{DRM(max)}$; $I_G=5mA$; $dI_G/dt=0.2A/\mu s$	-	2	-	μs
t_g	Crcuit commutated tum- off time	$V_{DM}=67\% V_{DRM(max)}$; $T_j=125^{\circ}C$; $I_{TM}=8A$ $V_R=10V$; $dI_{TM}/dt=10A/\mu s$ $DI_G/dt=2V/\mu s$; $R_{GK}=1k\Omega$	-	100	-	μs

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MECHANICAL DATA

Dimensions in mm
Net Mass: 2 g

